such a petition has been inadvertently overlooked and is required. As provided below, charge Deposit Account **04-1105** for any required fee.

Please amend the subject application as follows:

IN THE FIGURES

Please **replace** FIGs. 5A and 5B and FIGs. 6A through 6F with the enclosed figures. No new matter has been added. FIGs. 5A and 5B and FIGs. 6A and 6F have been amended to include a legend –PRIOR ART -- that is shown in red.

IN THE CLAIMS

Please **amend** the following claim:

6. (Amended) A method for producing a solid-state imaging device, wherein the device comprises:

a semiconductor substrate;

a light shielding section having an aperture for partially shielding light incident on a surface of the semiconductor substrate;

a light reception section for converting the light which is incident on the surface of the semiconductor substrate through the aperture to an electric charge; and

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a passivation section having a substantially flat top surface and overlying the light shielding section, the light reception section and the aperture so as to provide moisture and chemical resistance and to provide barrier properties against impurities, wherein the method comprises the steps of:

forming a thin film used for forming the passivation section on the light shielding section;

applying an SOG film to the thin film used for forming the passivation section; and

flattening a surface of the thin film to form the passivation section by performing an etchback technique under a condition that a selective ratio of the SOG film to the thin film used for forming the passivation section is about 1:1.

7. (Amended) A method for producing a solid-state imaging device, wherein the device comprises:

a semiconductor substrate;

a light shielding section having an aperture for partially shielding light incident on a surface of the semiconductor substrate;

a light reception section for converting the light which is incident on the surface of the semiconductor substrate through the aperture to an electric charge; and

a passivation section having a substantially flat top surface and overlying the light shielding section, the light reception section and the aperture so as to provide moisture and chemical resistance and to provide barrier properties against impurities, and an insulation section having a substantially flat top surface which is interposed between the passivation section and the light shielding section, wherein the method comprises the steps of:

forming the insulation section on the light shielding section;

flattening a surface of the insulation section by chemical machine polishing; and

forming the passivation section so as to have the substantially flat top surface by depositing a material used for forming the passivation section on the insulation section.

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8. (Amended) A method for producing a solid-state imaging device, wherein the device comprises:

a semiconductor substrate;

a light shielding section having an aperture for partially shielding light incident on a surface of the semiconductor substrate;

a light reception section for converting the light which is incident on the surface of the semiconductor substrate through the aperture to an electric charge;

a passivation section having a substantially flat top surface and overlying the light shielding section, a light reception section and the aperture;

an insulation section having a substantially flat top surface which is interposed between the passivation section and the light shielding section so as to provide

moisture and chemical resistance and to provide barrier properties against impurities, wherein the method comprises the steps of:

forming the insulation section so as to have the substantially flat top surface by applying an SOG film to the light shielding section and the aperture; and

forming the passivation section so as to have the substantially flat top surface by depositing a material used for forming the passivation section on the insulation section.

Please **add** the following new claims:

9. (New) A solid-state imaging device according to claim 1, wherein the passivation section comprises at least a SOG film.

10. (New) A solid-state imaging device according to claim 4, wherein the insulation section comprises at least a SOG film.

11. (New) A method according to claim 5, wherein the method further comprises the step of forming a SOG film to the passivation section.

12. (New) A method according to claim 7, wherein the method further comprises the step of forming a SOG film to the passivation section.

13. (New) A solid-state imaging device, comprising:

a semiconductor substrate;

a light shielding section having an aperture for partially shielding light incident on a surface of the semiconductor substrate;

a light reception section for converting the light which is incident on the surface of the semiconductor substrate through the aperture to an electric charge; and

a passivation section having a substantially flat top surface and overlying the light shielding section, the light reception section and the aperture so as to provide

moisture and chemical resistance and to provide barrier properties against impurities and others.

14. (New) A method for producing a solid-state imaging device, wherein the device comprises:

a semiconductor substrate;

a light shielding section having an aperture for partially shielding light incident on a surface of the semiconductor;

a light reception section for converting the light which is incident on the surface of the semiconductor substrate through the aperture to an electric charge; and

a passivation section having a substantially flat top surface and overlying the light shielding section, the light reception section and the aperture so as to provide moisture and chemical resistance and to provide barrier properties against impurities and others, wherein the method comprises the steps of:

forming a thin film used for forming the passivation section on the light shielding section and the aperture; and

flattening a surface of the thin film to form the passivation section by chemical machine polishing.

Marked-up versions of the amended passages from the specification and claims are provided in an annex to this amendment.

REMARKS

Claims 1 through 14 are pending in the subject application. Claims 1-8 stand rejected under 35 U.S.C. 103(a). Claims 6, 7, and 8 been amended. No new matter has been added to the application. Claims 9-14 have been newly added.